

## **DESCRIPTION**

These transistors are designed for general purpose amplifier applications. They are housed in the SC-70 which is designed for low power surface mount applications.

The MBT3904W is available in SC-70 package.

## **FEATURES**

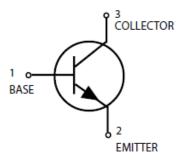
- ROHS compliance
- Available in SC-70 package

## ORDERING INFORMATION

Package Type	Part Number		
SC-70	MBT3904W		
Note 3,000pcs/ Reel			
AiT provides all RoHS Compliant Products			

# PIN DESCRIPTION

#### NPN MBT3904W



## **ABSOLUTE MAXIMUM RATINGS**

V <sub>CEO</sub> , Collector-Emitter Voltage	40Vdc
V <sub>CBO</sub> , Collector-Base Voltage	60Vdc
V <sub>EBO</sub> , Emitter-Base Voltage	6.0Vdc
I <sub>C</sub> , Collector Current-Continuous	200mAdc

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## THERMAL CHARACTERISTICS

Parameter	Symbol	Max	Unit
Total Package DissipationNOTE1			
T <sub>A</sub> = 25°C	PD	150	mW
Thermal Resistance, Junction to Ambient	Reja	833	°C/W
Junction and Storage Temperature	TJ, Tstg	-55 to +150	°C

NOTE1: Device mounted on FR4 glass epoxy printed circuit board using the minimum recommended footprint

# **ELECTRICAL CHARACTERISTICS**

T<sub>A</sub> = 25°C unless otherwise noted

Parameter	Symbol	Conditions	Min	Max	Unit	
OFFCHARACTERISTICS						
Collector–Emitter	V <sub>(BR)CEO</sub> I <sub>C</sub> = 1.0mAdc, I <sub>B</sub> = 0		40		\	
Breakdown Voltage NOTE1	V (BR)CEO	IC - T.UITIAUC, IB - U	40	-	Vdc	
Collector-Base Breakdown	V <sub>(BR)CBO</sub>	 	60	-	Vdc	
Voltage	V (BR)CBO	$I_C = 10\mu Adc$ , $I_E = 0$	00			
Emitter-Base Breakdown	$V_{(BR)EBO}$	$I_{E} = 10 \mu Adc, I_{C} = 0$	6.0	-	Vdc	
Voltage	V (BR)EBO	IE - ΤΟμΑας, IC - 0	0.0			
Base Cutoff Current	$I_{BL}$	$V_{CE}$ = 30Vdc, $V_{EB}$ = 3.0Vdc	-	50	nAdc	
Collector Cutoff Current	ICEX	$V_{CE}$ = 30Vdc, $V_{EB}$ = 3.0Vdc	-	50	nAdc	
ONCHARACTERISTICSNOTE	2					
	h <sub>FE</sub>	$I_C = 0.1 \text{mAdc}, V_{CE} = 1.0 \text{Vdc}$	40	-	-	
		$I_C = 1.0 \text{mAdc}, V_{CE} = 1.0 \text{Vdc}$	70	-		
DC Current Gain		$I_C$ = 10mAdc, $V_{CE}$ = 1.0Vdc	100	300		
		$I_C$ = 50mAdc, $V_{CE}$ = 1.0Vdc	60	ı		
		$I_C$ = 100mAdc, $V_{CE}$ = 1.0Vdc	30	-		
Collector–Emitter		I <sub>C</sub> = 10mAdc, I <sub>B</sub> = 1.0mAdc	-	0.2		
Saturation Voltage	$V_{CE(SAT)}$	$I_C = 50$ mAdc, $I_B = 5.0$ mAdc	-	0.3	Vdc	
Base–Emitter Saturation	\/	$I_C = 10$ mAdc, $I_B = 1.0$ mAdc	0.65	0.85	\/da	
Voltage	$V_{BE(SAT)}$	$I_C$ = 50mAdc, $I_B$ = 5.0mAdc	-	0.95	Vdc	

NOTE2: Pulse Test: Pulse Width≤300µs; Duty Cycle≤2.0%.

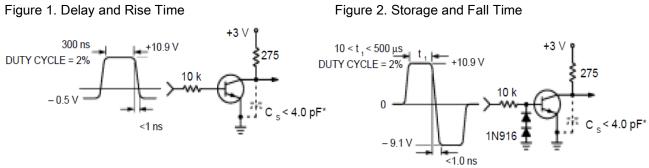
## $T_A = 25$ °C unless otherwise noted

Parameter	Symbol	Conditions	Min	Max	Unit
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain-Bandwidth Product	f⊤	Ic=10mAdc, VcE=20Vdc,f=100MHz		-	MHz
Output Capacitance	Сово	V <sub>CB</sub> = 5.0Vdc, I <sub>E</sub> = 0,f = 1.0MHz	-	4.0	pF
Input Capacitance	Сіво	V <sub>EB</sub> = 0.5Vdc, I <sub>C</sub> = 0, f = 1.0MHz	-	8.0	pF
Input Impedance	h <sub>IE</sub>	V <sub>CE</sub> = 10Vdc, I <sub>C</sub> =1.0mAdc,f = 1.0kHz	1.0	10	ΚΩ
Voltage Feedback Ratio	h <sub>RE</sub>	V <sub>CE</sub> = 10Vdc, I <sub>C</sub> =1.0mAdc,f = 1.0kHz		8.0	X 10 <sup>-4</sup>
Small–Signal Current Gain	h <sub>FE</sub>	V <sub>CE</sub> =10Vdc, I <sub>C</sub> = 1.0mAdc,f = 1.0kHz	100	400	-
Output Admittance	hoe	$V_{CE}$ =10Vdc, $I_C$ = 1.0mAdc,f = 1.0kHz	1.0	40	μΩ
Noise Figure	NF	$V_{CE}$ = 5.0Vdc, $I_{C}$ =100 $\mu$ Adc, $R_{S}$ =1.0k $\Omega$ , $f$ =1.0kHz	-	5.0	dB
SWITCHING CHARACTERISTICS					
Delay Time	t⊳	V <sub>CC</sub> = 3.0Vdc, V <sub>BE</sub> =-0.5Vdc		35	ns
Rise Time	t <sub>R</sub>	I <sub>C</sub> = 10mAdc, I <sub>B1</sub> = 1.0mAdc		35	ns
Storage Time	<b>t</b> s	V <sub>CC</sub> = 3.0Vdc, I <sub>C</sub> =10mAdc		200	ns
Fall Time	t⊧	$I_{B1} = I_{B2} = 1.0 \text{mAdc}$ 50		50	ns

### TYPICAL CHARACTERISTICS

#### **Equivalent Test Circuit**

Figure 1. Delay and Rise Time



\*Total shunt capacitance of test jig and connectors

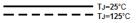


Figure 3. Capacitance

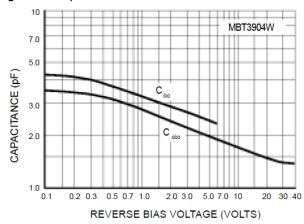


Figure 5. Turn-On Time

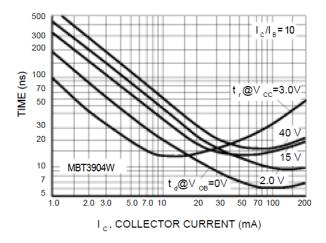
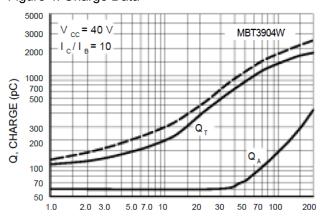
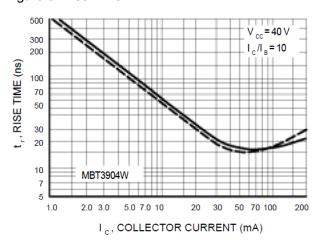


Figure 4. Charge Data



I c, COLLECTOR CURRENT (mA)

Figure 6. Rise Time



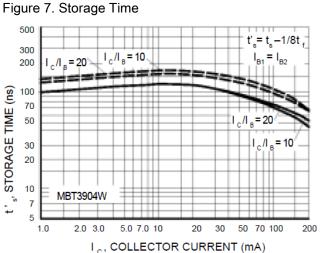


Figure 8. Fall Time 500 300 200 100 70 t, FALL TIME (ns) 50 30 20 10 MBT3904W 5 1.0 2.0 3.0 5.0 7.0 10 30 50 70 100

I c, COLLECTOR CURRENT (mA)

#### TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

V<sub>CE</sub> = 5.0Vdc, T<sub>A</sub> = 25°C, Bandwidth =1.0 Hz

Figure 9. Noise Figure

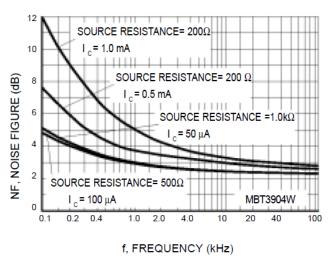
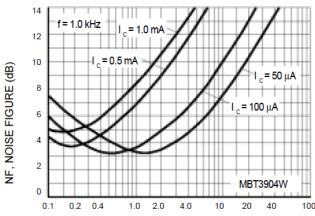


Figure 10. Noise Figure



R  $_{\rm s}$  , SOURCE RESISTANCE (k $\Omega$ )

### **h PARAMETERS** $V_{CE} = 10Vdc$ , f = 1.0kHz, $T_A = 25$ °C

Figure 11. Current Gain

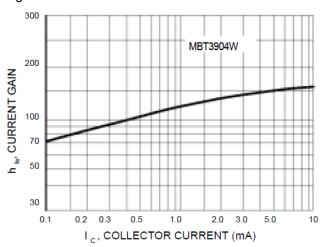


Figure 13. Input Impedance

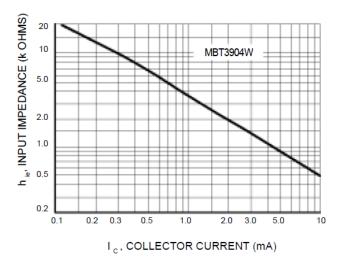


Figure 12. Output Admittance

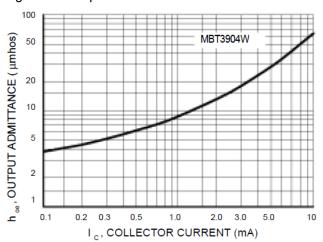
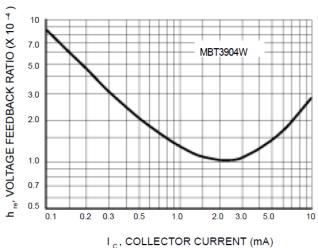


Figure 14. Voltage Feedback Ratio



#### TYPICAL STATIC CHARACTERISTICS

Figure 15. DC Current Gain

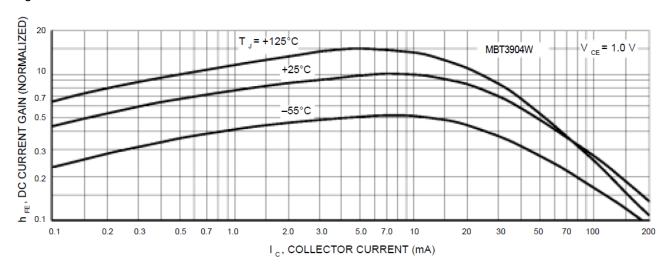


Figure 16. Collector Saturation Region

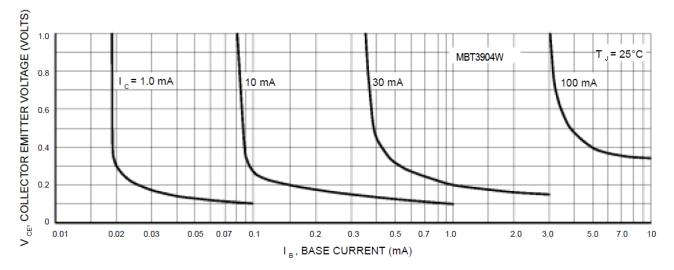


Figure 17. "ON" Voltages

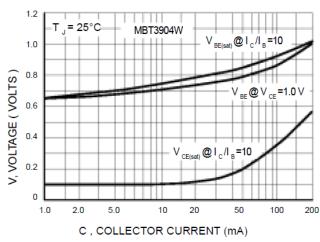
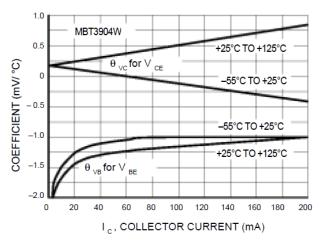
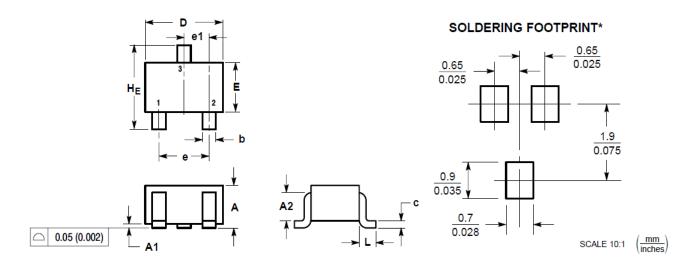


Figure 18. Temperature Coefficients



# PACKAGE INFORMATION

Dimension in SC-70 Package (Unit: mm)



DIM	MILLIMETERS		INCHES		
	MIN	MAX	MIN	MAX	
Α	0.80	1.00	0.032	0.040	
A1	0.00	0.10	0.000	0.004	
A2	0.7 REF		0.028 REF		
b	0.30	0.40	0.012	0.016	
С	0.10	0.25	0.004	0.010	
D	1.80	2.20	0.071	0.087	
Е	1.15	1.35	0.045	0.053	
е	1.20	1.40	0.047	0.055	
e1	0.65 BSC		0.026 BSC		
L	0.425 REF		0.017 REF		
HE	2.00	2.40	0.079 0.095		

## IMPORTANT NOTICE

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